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PN - JP2002313076 A 20021025
TI - FERROELECTRIC MEMORY DEVICE
AB - PROBLEM TO BE SOLVED: To realize a ferroelectric memory device by which occurrence of imprint in a ferroelectric memory cell can be detected by using a simpler and smaller scale circuit than a Sawyer-Tower circuit.
- SOLUTION: The occurrence of imprint can surely be detected by using a simpler and smaller scale circuit than the Sawyer-Tower circuit by providing a preserved temperature measuring circuit 3 for judging whether the imprint is caused in the ferroelectric memory cell of a memory cell section 2 or not based on data of accumulated stress caused by high temperature preservation of the ferroelectric memory device itself. The size of the ferroelectric memory device can be made small.
I - G11C11/22
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ABD - 20030205
ABV - 200302
AP - JP20010117905 20010417